2SC3679

Silicon NPN Triple Diffused Planar Transistor (High Voltage Switching Transistor)

Application: Switching Regulator and General Purpose

Absolute	(Ta=25°C)	
Symbol	2SC3679	Unit
Vсво	900	V
VCEO	800	V
VEBO	7	V
Ic	5(Pulse10)	А
Ів	2.5	А
Pc	100(Tc=25°C)	W
Tj	150	°C
Tstg	-55 to +150	°C

Electrical Cl	haracteristics	(Ta=25°C)		
Symbol	Conditions	2SC3679	Unit	
Ісво	Vcb=800V	100max	μΑ	
Г ЕВО	VEB=7V	100max	μΑ	
V(BR)CEO	Ic=10mA	800min	V	
hfe	Vce=4V, Ic=2A	10 to 30		
Vce(sat)	Ic=2A, IB=0.4A	0.5max	V	
VBE(sat)	Ic=2A, IB=0.4A	1.2max	V	
fT	Vce=12V, Ie=-0.5A	6typ	MHz	
Сов	VcB=10V, f=1MHz	75typ	рF	

a. Type No. b. Lot No.

External Dimensions MT-100(TO3P)

■Typical Switching Characteristics (Common Emitter)

Vcc (V)	R _L (Ω)	Ic (A)	V _{BB1} (V)	V _{BB2} (V)	IB1 (A)	IB2 (A)	ton (µs)	tstg (µs)	tf (µs)
250	125	2	10	-5	0.3	-1	1max	5max	1max

















